

20 V, 2 A P-channel Trench MOSFET Rev. 1 — 28 June 2011

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching

1.3 Applications

- Relay driver
- High-speed line driver

- Trench MOSFET technology
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Quick reference data						
Parameter	Conditions		Min	Тур	Max	Unit
drain-source voltage	T _j = 25 °C		-	-	-20	V
gate-source voltage			-12	-	12	V
drain current	V_{GS} = -4.5 V; T_j = 25 °C	<u>[1]</u>	-	-	-2	А
aracteristics						
drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C		-	90	115	mΩ
	drain-source voltage gate-source voltage drain current aracteristics drain-source on-state	$\begin{array}{c} \text{drain-source voltage} & T_j = 25 \ ^{\circ}\text{C} \\ \text{gate-source voltage} \\ \text{drain current} & V_{\text{GS}} = -4.5 \ \text{V}; \ \text{T}_j = 25 \ ^{\circ}\text{C} \\ \end{array}$	drain-source voltage gate-source voltage $T_j = 25 \text{ °C}$ drain current $V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$ aracteristicsdrain-source on-state $V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	$\begin{array}{c} \mbox{drain-source voltage} & T_j = 25 \ ^{\circ}\ C & -12 \\ \mbox{gate-source voltage} & V_{GS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}\ C & 11 \\ \mbox{aracteristics} & & \\ \mbox{drain-source on-state} & V_{GS} = -4.5 \ V; \ I_D = -2 \ A; \ T_j = 25 \ ^{\circ}\ C & - \end{array}$	drain-source voltage gate-source voltageT_j = 25 °C-drain current $V_{GS} = -4.5 V; T_j = 25 °C$ -12drain current $V_{GS} = -4.5 V; T_j = 25 °C$ -drain-source on-state $V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C$ -	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	D	drain		
3	G	gate		
4	S	source		
5	D	drain		Ś
6	D	drain	SOT363 (TSSOP6)	017aaa094

3. Ordering information

Table 3. Orde	ering information		
Type number	Package		
	Name	Description	Version
PMG85XP	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
PMG85XP	YA%

[1] % = placeholder for manufacturing site code

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5. Limiting values

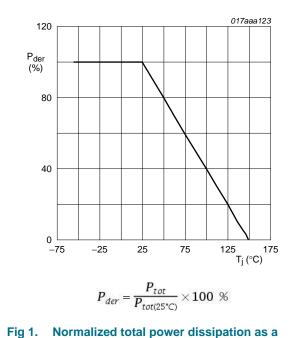
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

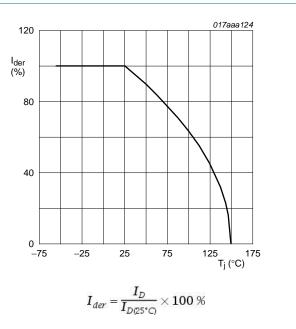
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	$T_j = 25 \ ^{\circ}C$		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _j = 25 °C	<u>[1]</u>	-	-2	А
		V _{GS} = -4.5 V; T _j = 100 °C	<u>[1]</u>	-	-1.3	А
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$		-	-8	А
P _{tot} total power dissipation	total power dissipation	T _{amb} = 25 °C	[2]	-	375	mW
			[1]	-	725	mW
		T _{sp} = 25 °C		-	2400	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
ls	source current	T _{amb} = 25 °C	[1]	-	-0.7	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

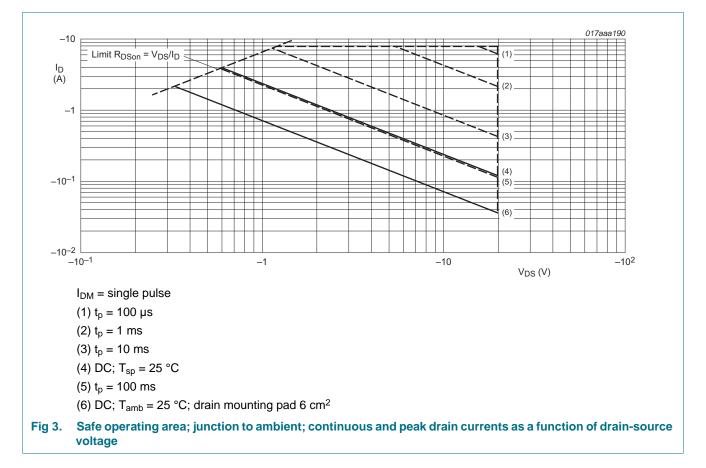


function of junction temperature





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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	<u>[1]</u>	-	290	334	K/W
	from junction to ambient		[2]	-	150	173	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	45	52	K/W

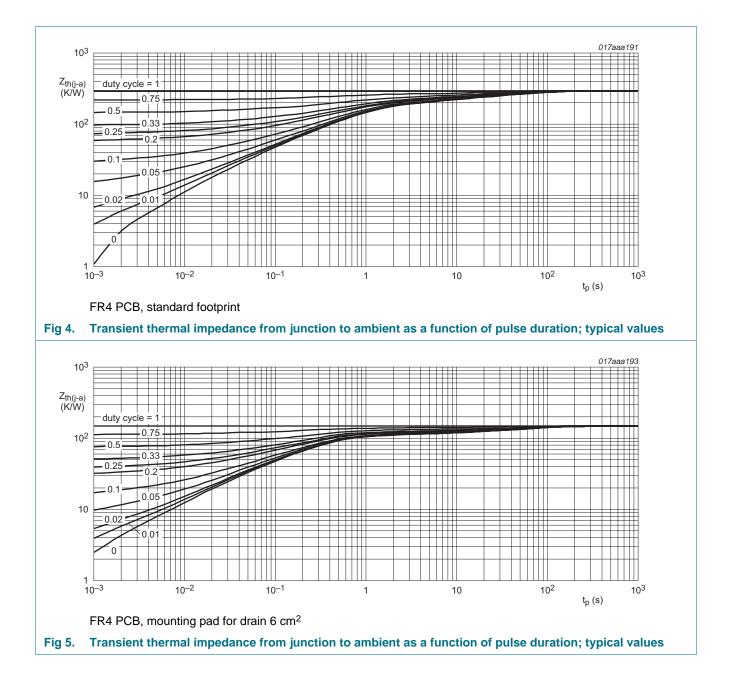
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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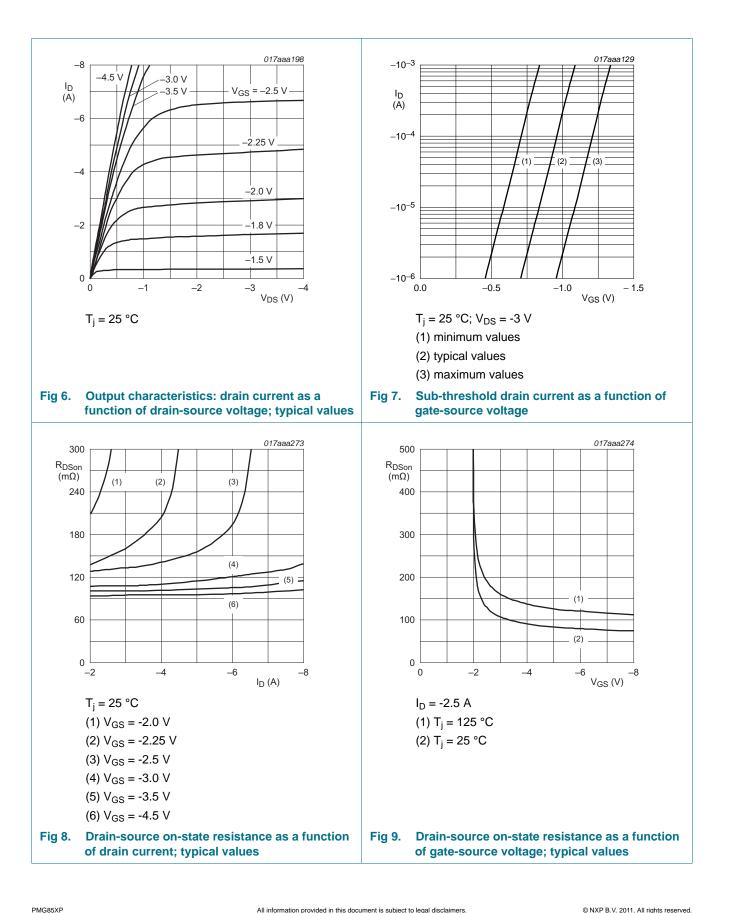


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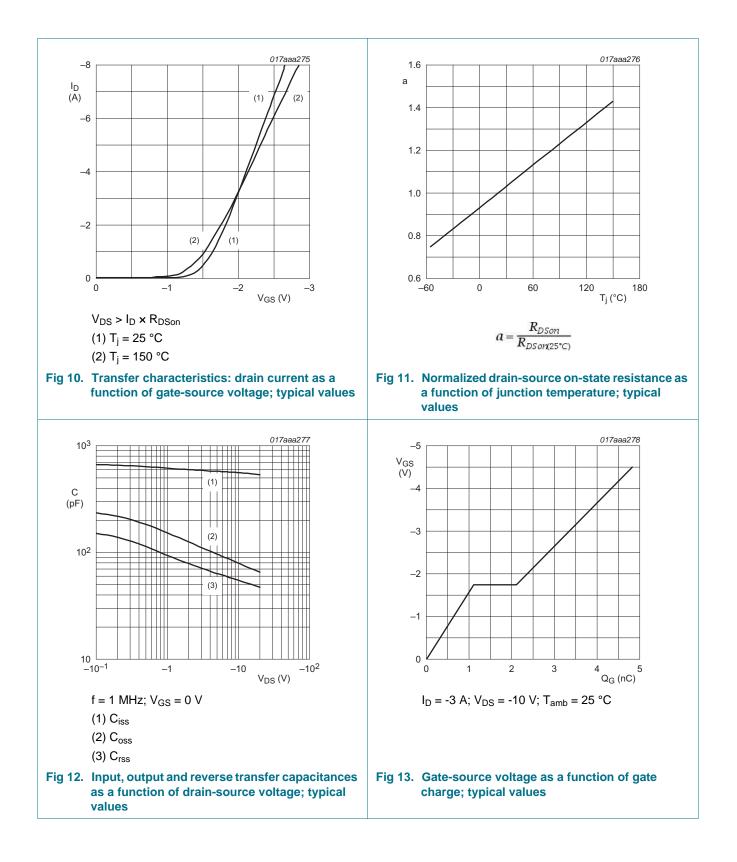
7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.65	-0.9	-1.15	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-15	μA
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C	-	90	115	mΩ
	resistance	V_{GS} = -4.5 V; I _D = -2 A; T _j = 150 °C	-	130	166	mΩ
		V_{GS} = -2.5 V; I_D = -2 A; T_j = 25 °C	-	125	160	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; \text{ I}_{D} = -2 \text{ A}; \text{ T}_{j} = 25 \text{ °C}$	-	6.3	-	S
Dynamic of	characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; \text{ I}_{D} = -1 \text{ A}; \text{ V}_{GS} = -4.5 \text{ V};$	-	4.8	7.2	nC
Q _{GS}	gate-source charge	$T_j = 25 \ ^{\circ}C$	-	1.1	-	nC
Q _{GD}	gate-drain charge		-	1	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}; \text{ f} = 1 \text{ MHz}; \text{ V}_{GS} = 0 \text{ V};$	-	560	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	80	-	pF
C _{rss}	reverse transfer capacitance		-	55	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω ;	-	13	-	ns
t _r	rise time	$T_j = 25 \text{ °C}; I_D = -2.5 \text{ A}$	-	35	-	ns
t _{d(off)}	turn-off delay time		-	39	-	ns
t _f	fall time		-	25	-	ns
Source-dr	ain diode					
V _{SD}	source-drain voltage	I _S = -0.7 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

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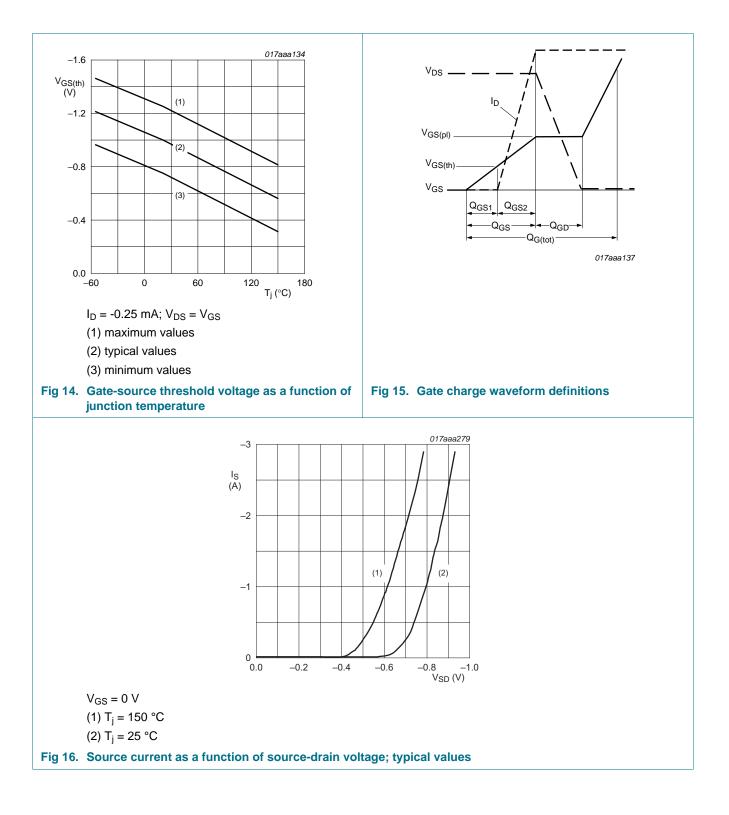
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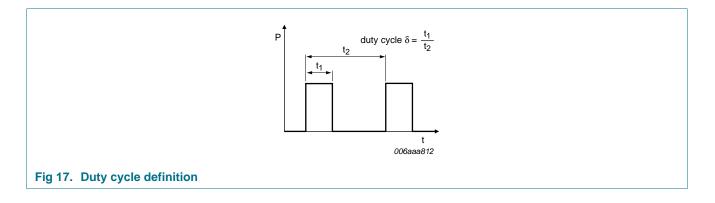
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8. Test information



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9. Package outline

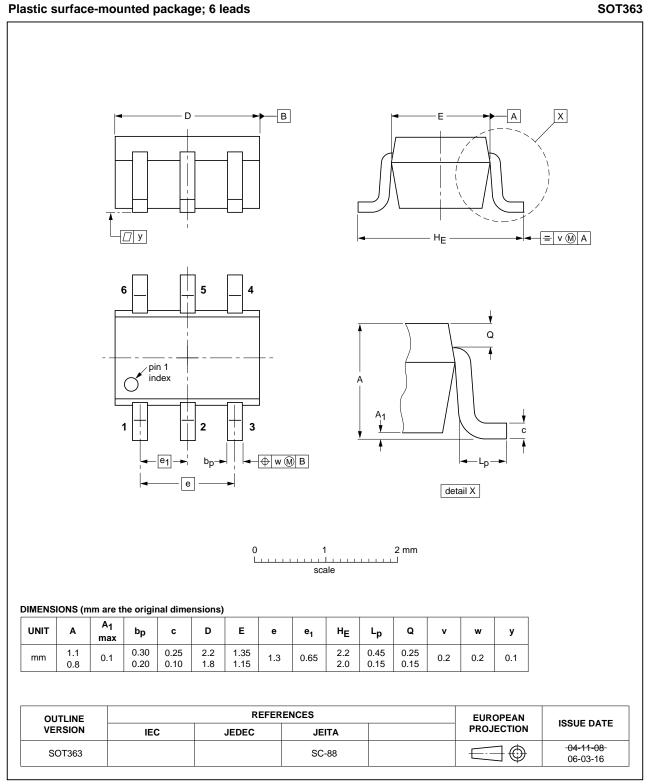
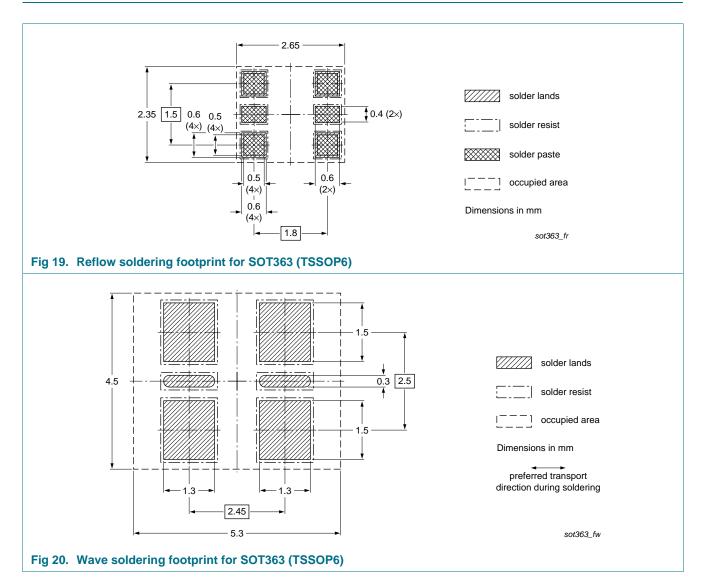


Fig 18. Package outline SOT363 (TSSOP6)

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10. Soldering



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11. Revision history

Table 8. Revis	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PMG85XP v.N	20110628	Product data sheet	-	-			

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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